

Technical Data Data Sheet N0229, Rev. -

ŠŠ12 THRU SS110 SCHOTTKY RECTIFIER

Features:

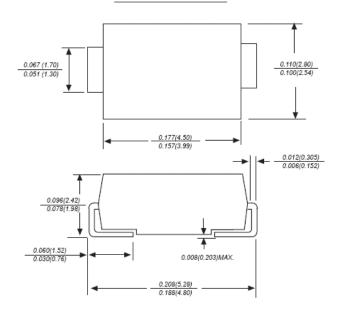
- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Metal silicon junction, majority carrier conduction
- Low Power Loss, High Efficiency
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed:250 C/10 seconds at terminals
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data:

- Case: JEDEC SMA molded plastic body
- Terminals: leads solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Weight: 0.003 ounce, 0.093 grams
- Mounting Position: Any

Mechanical Dimensions (In mm / Inches)

DO-214AC/SMA



Dimensions in inches and (millimeters)

OPTION 1



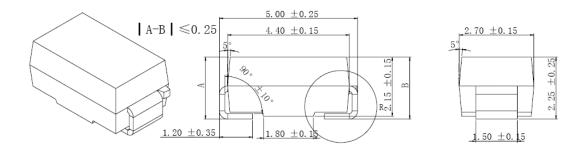
SS12

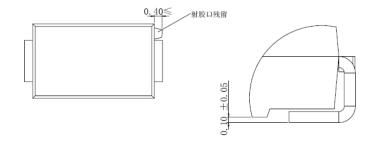
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OPTION 2(JK)

SMA

MARKING, MOLDING RESIN Marking for SS12/13/14/15/16/18/110, 1st row SS12/13/14/15/16/18/110, 2nd row YYWWL Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number



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Ordering Information:

Device	Package	Shipping
SS12 THRU SS110	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings and Electrical Characteristics

Ratings at 25 C ambient temperature unless otherwise specified. Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	SS12	SS13	SS14	SS15	SS16	SS18	SS110	UNITS
Maximum repetitive peak reverse voltage		20	30	40	50	60	80	100	VOLTS
Maximum RMS voltage		14	21	28	35	42	56	70	VOLTS
Maximum DC blocking voltage		20	30	40	50	60	80	100	VOLTS
Maximum average forward rectified current at TL(see fig.1)		1.0						Amp	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)		30.0						Amps	
Maximum instantaneous forward voltage at 1.0A	VF	0.45	0.55		0.70		0.85		Volts
Maximum DC reverse current Ta=25 C at rated DC blocking voltage Ta=100 C	lĸ	0.5					.0	mA	
Typical junction capacitance (NOTE 1)	CJ	110 90					рF		
Typical thermal resistance (NOTE 2)		88.0							Ċ/W
Operating junction temperature range		-65 to +125 -65 to +150					С		
Storage temperature range		-65 to +150						С	

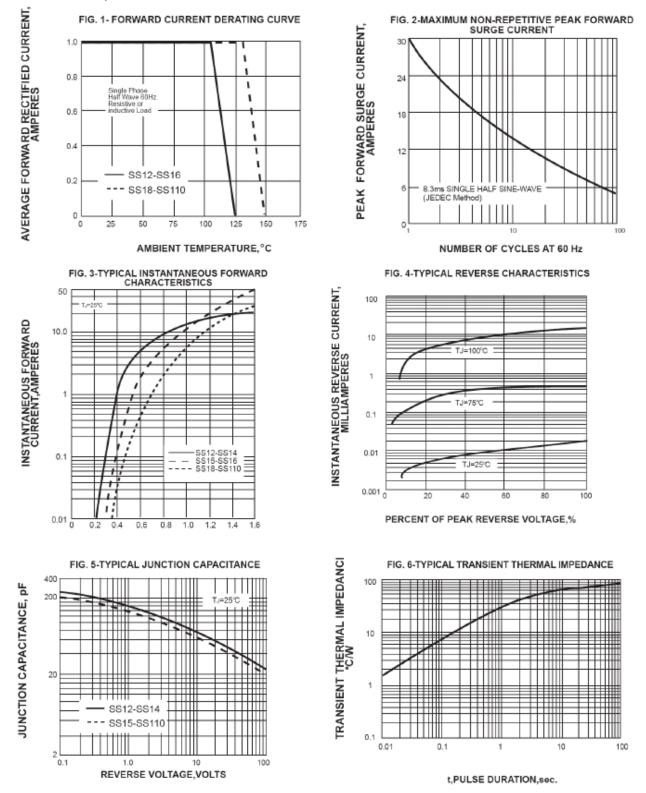
Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas



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